

AMENDMENT TO THE CLAIMS:

This listing of the claims will replace all prior versions, and listings, of claims in the application.

LISTING OF CLAIMS:

Claims 1-23. (Canceled)

Claim 24 (Original) An electrical contact to a region of a silicon-containing substrate comprising a substrate having an exposed region of a silicon-containing semiconductor material; and a first layer of Ni monosilicide, wherein said substrate and said first layer are separated by a Si-Ge interlayer and said first layer of Ni monosilicide comprises 0.01 to 50 atomic percent of at least one alloy additive selected from the group consisting of C, Al, Si, Sc, Ti, V, Cr, Mn, Fe, Co, Y, Zr, Nb, Mo, Ru, Rh, Pd, In, Sn, La, Hf, Ta, W, Re, Ir, Pt, Ce, Pr, Nd, Sm, Eu, Gd, Tb, Dy, Ho, Er, Tm, Tb and Lu.

Claim 25 (Previously Presented) The electrical contact of Claim 24 wherein said silicon-containing semiconductor material comprises single crystal Si, polycrystalline Si, SiGe, amorphous Si or a silicon-on-insulator (SOI).

Claims 26-27 (Canceled)

Claim 28 (Previously Presented) The electrical contact of Claim 24 wherein said substrate is doped.

Claim 29 (New) The electrical contact of Claim 24 wherein said substrate includes a p⁺ silicon area.

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Claim 30 (New) The electrical contact of Claim 24 wherein said substrate includes a n⁺ silicon area.

Claim 31 (New) The electrical contact of Claim 24 wherein said at least one alloy additive is C, Al, Si, Sc, Ti, V, Cr, Mn, Fe, Co, Cu, Y, Zr, Nb, Mo, Ru, Rh, Pd, In, Sn, La, Hf, Ta, W, Re, Ir or Pt.

Claim 32 (New) The electrical contact of Claim 31 wherein said at least one additive is Si, Ti, V, Cr, Nb, Rh, Ta, Re or Ir.

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